Abstract

Semiconductor substrate and semiconductor circuit formed therein and associated fabrication methods

The invention relates to a semiconductor substrate and to a semiconductor circuit formed therein and associated fabrication methods, a multiplicity of depressions (P) with a respective dielectric layer (D) and a capacitor electrode (E2) being formed for realizing buried capacitors in a carrier substrate (1) and an actual semiconductor component layer (3) being insulated from the carrier substrate (1) by an insulation layer (2).

(Figure 1D)

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